Silicon PNP Power Transistors 2SB757

DESCRIPTION

- With TO-3PN package
- High collector current
- Wide area of safe operation
- Complement to type 2SD847

APPLICATIONS

- Audio amplifications
- Serie regulators
- General purpose power amplifiers

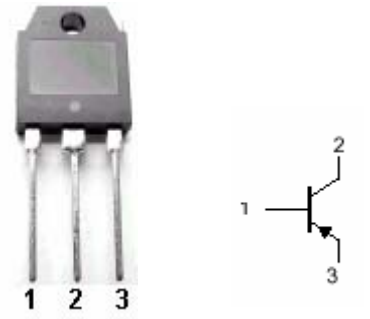

Fig.1 simplified outline (TO-3PN) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings(Tc=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-40	V
V_{CEO}	Collector-emitter voltage	Open base	-40	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-15	A
I_B	Base current		-5	A
P_C	Collector power dissipation	T_C=25℃	80	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance from junction to case	1.56	℃/W

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-0.1mA; I_E=0	-40			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA; I_B=0	-40			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-0.1mA; I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-5A; I_B=-0.5A			-0.8	V
V_{BEsat}	Base-emitter on voltage	I_C=-5A; I_B=-0.5A			-1.8	V
I_{CBO}	Collector cut-off current	V_{CB}=-40V; I_E=0			-10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-100	μA
h_{FE}	DC current gain	I_C=-5A ; V_{CE}=-2V	40		240	

Switching times

t_{on}	Turn-on time	I_C=-15A;I_{B1}=-I_{B2}=-1.5A R_L=2Ω;P_W=20μs,Duty≤2%			1.0	μs
t_s	Storage time				2.0	μs
t_f	Fall time				1.0	μs

PACKAGE OUTLINE

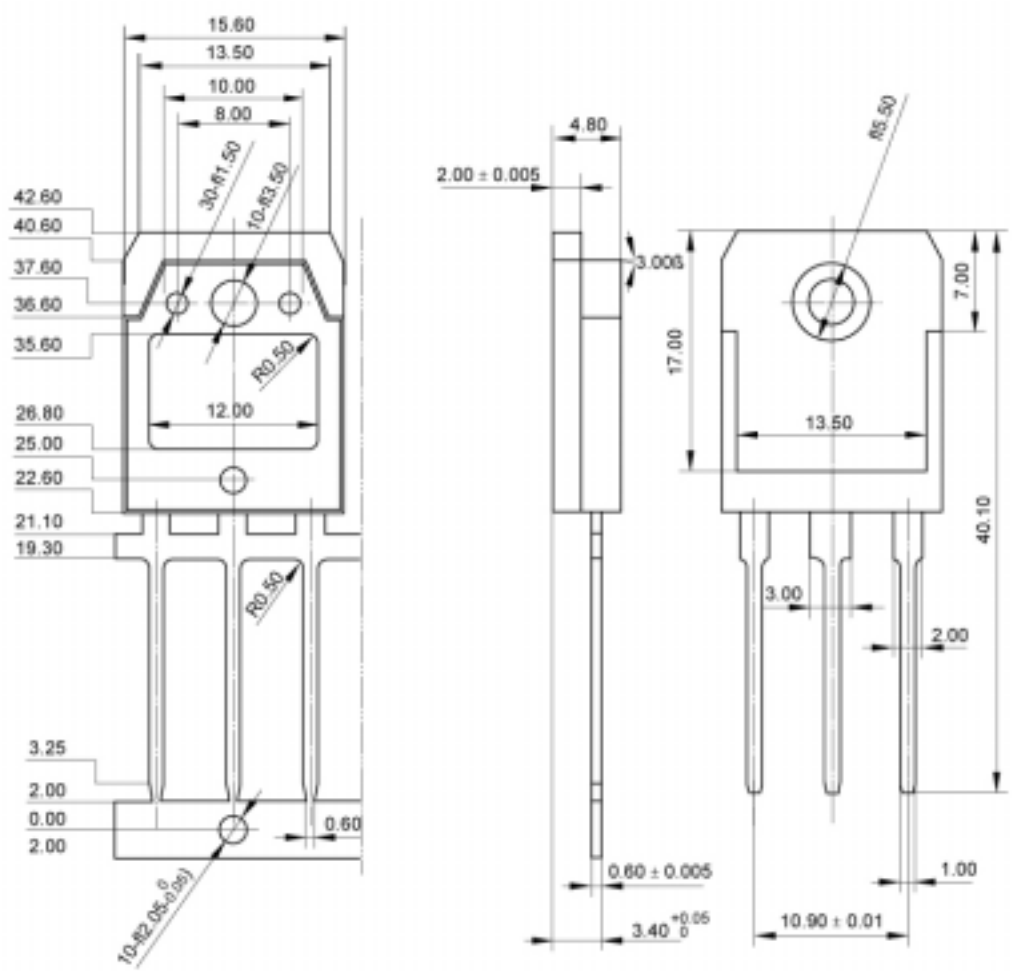

Fig.2 outline dimensions